Elodie Ghegin

List of Publications by Year
in descending order

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25 papers	165 citations	1307594 7 h-index	1281871 11 g-index
25 all docs	25 docs citations	25 times ranked	178 citing authors

#	Article	IF	Citations
1	Study of the Ti/InGaAs solid-state reactions: Phase formation sequence and diffusion schemes. Materials Science in Semiconductor Processing, 2020, 113, 105038.	4.0	3
2	Development of a CMOS-compatible contact technology for IIIâ€“V materials and Si photonics. Japanese Journal of Applied Physics, 2020, 59, SL0801.	1.5	2
3	Building blocks of silicon photonics. Semiconductors and Semimetals, 2019, 101, 1-41.	0.7	3
4	3D atomic-scale investigation of carbon segregation in phosphorus co-implanted silicon. Applied Physics Letters, 2019, 115, .	3.3	4
5	Pre-Amorphization Implants and in-situ Surface Preparation Optimization for Low Co-Silicided Area Density. , 2019, , .		0
6	Hybrid IIIâ€“V/Silicon Technology for Laser Integration on a 200-mm Fully CMOS-Compatible Silicon Photonics Platform. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-10.	2.9	44
7	Characterization of Heated Ion Implantation for non Amorphizing Conditions and Correlation with Kinetic Monte Carlo Simulations. , 2018, , .		2
8	CMOS-Compatible Contacts for Si Photonics from Solid-State Reaction to Laser Integration. , 2018, , .		1
9	CMOS-compatible contact technology for Si photonics. , 2018, , .		3
10	200mm full CMOS-compatible hybrid III-V/Si laser process integration on a mature silicon-photonic platform (Conference Presentation). , 2018, , .		1
11	CMOS-Compatible Contacts to n-InP. IEEE Transactions on Electron Devices, 2017, 64, 4408-4414.	3.0	13
12	Phase formation sequence in the Ti/InP system during thin film solid-state reactions. Journal of Applied Physics, 2017, 121, .	2.5	8
13	Hybrid III-V/Si DFB laser integration on a 220 mm fully CMOS-compatible silionn photonlcsplotform. , 2017, , .		7
14	Formation of Ni3InGaAs phase in Ni/InGaAs contact at low temperature. Applied Physics Letters, 2016, 109, 131902.	3.3	10
15	Phase formation in the Ni/nâ€“InP contacts for heterogeneous III/V-silicon photonic integration. Microelectronic Engineering, 2016, 156, 86-90.	2.4	12
16	Metallurgical studies of integrable Ni-based contacts for their use in IIIâ€“V/Si heterogeneous photonics devices. , 2016, , .		4
17	Considerations on fermi-depinning, dipoles and oxide tunneling for oxygen-based dielectric insertions in advanced CMOS contacts. , 2016, , .		0
18	Towards contact integration for IIIâ€“V/Silicon heterogeneous photonics devices. , 2016, , .		4

#	Article	IF	Citations
19	High performance CMOS FDSOI devices activated at low temperature. , 2016, , .		11
20	In situ cleaning of InGaAs surfaces prior to low contact resistance metallization. Microelectronic Engineering, 2016, 156, 91-96.	2.4	10
21	In situ cleaning/passivation of surfaces for contact technology on III-V materials. , 2015, , .		0
22	Solid state reaction of Ni thin film on n-InP susbtrate for III-V laser contact technology. , 2015, , .		0
23	InGaAs surface pretreatment prior to metal solid-state reactions for low resistance contacts. , 2015, , .		1
24	Elaboration of Ni/InP contacts: Solid state reactions and associated mechanisms. , 2015, , .		1
25	Cleaning of InGaAs and InP Layers for Nanoelectronics and Photonics Contact Technology Applications. ECS Transactions, 2015, 69, 251-259.	0.5	21